

# IMFEDK 2022 Program

**Nov, 28 (Mon)**

# Opening

10:00-10:05 Opening Remarks Mutsumi Kimura (Ryukoku University)

# **Keynote Speech-I**

## **Chair: Mutsumi Kimura**

10:05-10:45

- ## IN01 <Invited> Lessons Learned in Omnidirectional Co-Design of Neuromorphic Systems

Catherine D. Schuman,  
(University of Tennessee)

<Online>

**General Session - Emerging 1 -** Chair: Takeshi Fukuda

10:45-11:25

- IN08 <Invited> Algorithm/Hardware Co-design for Reliable AI

Shinya Takamaeda,  
(University of Tokyo)

11:25-11:45

- R07 *Monolithic Integration of GaN-based Optocoupler*

Chengshiun Liou and Chingfu Tsou,  
(Feng Chia University)

11·45-12·05

- ## R08 *Multi-Channel Near-Infrared Bandpass Mosaic Filter for Spectral Fundus Imaging*

Honghao Tang, Hironari Takehara, Yusuke Horiki, Makito Haruta, Hiroyuki Tashiro, Kiyotaka Sasagawa and Jun Ohta,  
(NAIST)

12·05-12·25

- R11 Carrier Control of  $In_2O_3$  TFT Fabricated by Atomic Layer Deposition

Yuto Kawato, Mutsunori Uenuma, Takanori Takahashi and Yukiharu Uraoka,  
(NAIST)

## 12:25-13:30      Lunch

### General Session - Compound 1 - Chair: Mutsunori Uenuma

13:30-14:10

- IN05    **<Invited> Progress and Challenges of Vertical GaN Power Devices on GaN Substrates**

Tohru Oka,  
(Toyoda Gosei)

14:10-14:50

- IN06    **<Invited> Demonstration of E-mode Operation in EID AlGaN/GaN MOS-HEMT**

Takuma Nanjo, Tomohiro Shinagawa, Masayuki Furuhashi, Kazuyasu Nishikawa and Takashi Egawa,  
(Mitsubishi Electric)

14:50-15:10

- R12    **Quasi-Normally-Off operation via Selective Area Growth in high-K-insulated GaN MIS-HEMTs**

S. Maeda, J. T. Asubar, I. Nagase, S. Urano, T. Nezu, T. Igarashi, A. Baratov, A. Yamamoto and M. Kuzuhara,  
(University of Fukui)

## 15:10-15:30   Short Break

### General Session - Compound 2 -      Chair: Hidetoshi Ishida

15:30-16:10

- IN07    **<Invited> Mist chemical vapor deposited-gate insulators for GaN-based MIS devices applications**

Zenji Yatabe, Joel T. Asubar and Yusui Nakamura,  
(Kumamoto University)

16:10-16:30

- R13    **Effect of High-Temperature Annealed Al<sub>2</sub>O<sub>3</sub> insulator on GaN MIS-HEMTs performance**

David Lau Bi Da, S. Yamazaki, S. Urano, A. Baratov, J. T. Asubar and M. Kuzuhara,  
(University of Fukui)

16:30-16:50

- R14 ***Effect of Oxygen plasma treatment on the performance of GaN-based MIS-HEMTs***

K. Sekiyama, M. Ishiguro, T. Nezu, S. Urano, A. Baratov, J. T. Asubar and M. Kuzuhara,  
(University of Fukui)

16:50-17:10

- R15 ***Improved Ohmic Contact Model for Accurate Simulation of GaN-based HEMTs Using Ensemble Monte Carlo Methods***

Kei Sakota, Kai Herbert, Kazuki Shibata, Masaaki Kuzuhara, Joel T. Asubar and Kazuki Kodama,  
(Kwansei Gakuin University)

## Nov, 29 (Tue)

### Poster Short Presentation

Chair: Joel T. Asubar

9:30-10:10

- P01 ***Combination of memristor and capacitor for synapse device in neuromorphic spiking computing***

T. Kuwahara, R. Oshio, H. Kawanishi, M. Kimura and Y. Nakashima,  
(Ryukoku University)

- P02 ***Gate Voltage Dependence of Quantum Electron Density Distribution for Nanosheet FETs***

Masashi Matsuda and Akira Hiroki,  
(Kyoto Institute of Technology)

- P03 ***The influence of the process parameters on the quality of SiO<sub>2</sub> film for the switching operation of ReRAM devices***

T. Taniyama and S. Sato,  
(Kansai university)

- P04 ***The Impact of Carrier Lifetime on the Electrical Characteristics of Z<sup>2</sup>-FET***

S. Kim and S. Sato,  
(Kansai university)

- P05 ***Detailed analysis of electrical components on SOI wafer with an ac pseudo-MOS method***

Y. Yifan and S. Sato,  
(Kansai university)

- P08 **Ga-Sn-O channel FeTFT with  $(Bi,La)_4Ti_3O_{12}$  as a single-layer ferroelectric gate**  
Ryoma Edahiro, Tomoki Fukui, Taiyo Shinoda, Hidenori Kawanishi, Tokiyoshi Matsuda and Mutsumi Kimura,  
(Ryukoku University)
- P09 **Alloying  $\beta-(Al_xGa_{1-x})_2O_3$  thin films grown on (010)  $\beta-Ga_2O_3$  substrates by mist CVD**  
Masahiro Kaneko, Hiroyuki Nishinaka, Yuki Kajita, Kazutaka Kanegae and Masahiro Yoshimoto,  
(Kyoto Institute of Technology)
- P10 **Atomic Structure of Gallium Oxide Layer at  $Al_2O_3/GaN$  Interface**  
Shingo Kuwaharada, Mutsunori Uenuma, Hiroto Tomita, Masaki Tanaka, Zexu Sun, Yusuke Hashimoto, Tomohiro Matsushita and Yukiharu Uraoka,  
(NAIST)
- P11 **Estimation of SPICE Parameters for MOSFETs with CNN Regression**  
Kohei Akazawa and Yoshinari Kamakura,  
(Osaka Institute of Technology)
- P12 **Monte Carlo Simulation of Electron Transport in SiC MOS Inversion Layers Considering Capture and Emission by Interface States**  
Fumitaka Tanaka, Hajime Tanaka and Nobuya Mori,  
(Osaka University)
- P13 **Development of a simulation framework for graphene nanoantenna based on finite-difference time-domain method**  
Shota Ogisawa and Satofumi Souma,  
(Kobe University)
- P14 **Development of Microfluidics Combined With a Cantilever Sensor Array for Multi-sample Detection**  
Y. Takahashi, K. Kamitani, R. Mitobe, T. Hasegawa, C. F. Werner, M. Sohgawa and M. Noda,  
(Kyoto Institute of Technology)
- P15 **Effect of Schottky Barrier at  $Fe_2VWAl/Si$  Interface on Thermoelectric Properties**  
Toshimitsu Maeda, Mutsunori Uenuma, Koki Enomoto and Yukiharu Uraoka,  
(NAIST)
- P16 **Ga-Sn-O thin-film device using mist CVD method and Spike-Timing-Dependent-Plasticity (STDP)**  
Norito Komai, Tetsuya Katagiri, Naoki Sahara, Kazuma Uno, Hidehito Kita, Tokiyoshi Matsuda, Hidenori Kawanishi and Mutsumi Kimura,  
(Ryukoku University)

- P17 ***Building process datasets for academic papers on bulk thermoelectric materials***  
Chowdhury Mohammad Mahir Asef, Mutsunori Uenuma, Hiroyuki Shindo, Yukiharu Uraoka, Shanshan Liu and Yuji Matsumoto,  
(NAIST)
- P18 ***Characterization of In-Ga-Zn-O thin film synapses for neuromorphic device using spike-timing-dependent-plasticity***  
Naoki Sahara, Tetuya Katagiri, Kenta Yachida, Kazuki Morigaki, Norito Komai, Tokiyoshi Matsuda, Hidenori Kawanishi and Mutumi Kimura,  
(Ryukoku University)
- P19 ***Optimization of deposition temperature for GTO thin film thermoelectric conversion devices using mist CVD method***  
Naoki Shibata, Ryo Ito, Yuhei Yamamoto, Hidenori Kawanishi, Tokiyoshi Matsuda and Mutumi Kimura,  
(Ryukoku University)
- P20 ***Metal electrode-dependent properties of a-IGZO ReRAM***  
Tetsuya Katagiri, Kazuki Morigaki, Kenta Yachida, Hidenori Kawanishi, Mutsumi Kimura and Tokiyoshi Matsuda,  
(Ryukoku University)
- P21 ***Analog and digital memristor characteristics in Ga-Sn-O three-layered ReRAM***  
Shu Shiomi, Daisuke Makioka, Hidenori Kawanishi, Tokiyohi Matsuda and Mutsumi Kimura,  
(Ryukoku University)
- P22 ***Evaluation of poly-Si TFT as an optical sensor***  
Yuise Sadamura and Mutumi Kimura,  
(Ryukoku University)

## 10:10-10:30 Short Break

## Keynote Speech-II

Chair: Hirobumi Watanabe

10:30-11:10

- IN02 ***<Invited> Future System Integration Technology Based on 3D Integration***  
Mitsumasa Koyanagi,  
(Tohoku University)

## General Session - Emerging 2 -

Chair: Minoru Noda

11:10-11:50

- IN09 **<Invited> Heat Storage Thermoelectric Generator for Wireless IoT Sensing Systems**

Takahito Ono, Nguyen Van Toan and Trung Thi Kim Tuoi,  
(Tohoku University)

<Online>

11:50-12:30

- IN10 **<Invited> Surface engineering of oxide nanostructures for efficient energy technologies**

Matthias T. Elm,  
(University of Giessen)

## 12:30-13:30 Lunch

## Special Session

### – Supported by IEEE SSCS Kansai Chapter –

Chair: Kazutoshi Kobayashi

13:30-14:10

- IN14 **<Invited> Embedded SRAM Design Challenges in Leading-Edge FinFET Technologies**

Koji Nii and Kazutoshi Kobayashi,  
(Kyoto Institute of Technology)

<Online>

14:10-14:50

- IN15 **<Invited> Investigation of Soft Error Sensitivity in EUV 7 nm FinFET Technology at Terrestrial Environment**

Taiki Uemura,  
(Samsung Electronics)

14:50-15:10

- R03 **Dual-Band Single-Output WLAN Directional Coupler in a SOI CMOS Process**

Ryangsu Kim, Kenta Seki and Kazuhito Osawa,  
(Murata Manufacturing Co., Ltd)

15:10-15:30

- R10 **Evaluation of Soft Error Tolerance on Flip-Flops Restoring from a Single Node Upset by C-elements**

Takafumi Ito, Ryuichi Nakajima, Jun Furuta and Kazutoshi Kobayashi,  
(Kyoto Institute of Technology)

## 15:30-15:50 Short Break

### General Session - Silicon 1 -

Chair: Naoteru Shigekawa

15:50-16:30

- IN04 **<Invited> Study on Fluorographene Charge Trapping layer for Nonvolatile Memory Applications**

Yuichiro Mitani, R. Kawashima, R. Ishikawa and H. Nohira,  
(Tokyo City University)

<Online>

16:30-16:50

- R04 **1/f Noise Characterizing Method of MOSFET Devices and Processes by the Power Spectral Density Integrated Method**

Yoshiki Murayama, Masato Kijima, Takehiko Yamashita, Yusuke Takezaki, Masanori Miyata, Ryuta Isobe and Hirobumi Watanabe,  
(Nissinbo Micro Devices Inc.)

### General Session - Emerging 3 -

Chair: Takatoshi Kato

16:50-17:10

- R01 **Polyimide-supported AlScN thin films based surface acoustic wave (SAW) delay line for flexible electronics**

KANOUNI Fares and LAIDOUDI Farouk,  
(Research center in Industrial Technologies, Algeria)

<Online>

17:10-17:30

- R02 **S2 Lamb-mode acoustic resonator with grooved micro-channels for liquids characterization**

Farouk Laidoudi, Fares Kanouni and Cinzia Caliendo,  
(Research center in Industrial Technologies, Algeria)

<Online>

**Nov, 30 (Wed)**

**General Session - Silicon 2 -**

Chair: Shunsuke Koba

9:30-10:10

- IN03 **<Invited> R&D of 3D-IC technology through the national project**  
Katsuya Kikuchi,  
(AIST)

10:10-10:30

- R06 **Modeling of Super Steep Subthreshold Slope Device by using Neural Network**  
Kengo Nakata, Takayuki Mori and Jiro Ida,  
(Kanazawa Institute of Technology)

10:30-10:50

- R09 **Effect of Post Deposition Annealing on Electrical Properties of GaO<sub>x</sub>/Si structure by Mist Chemical Vapor Deposition Method**  
Hidenobu Mori and Haruhiko Yoshida,  
(University of Hyogo)

**10:50-11:10 Short Break**

**Special Session**

**- IMFEDK Celebrating our 20th Anniversary -**

Chair: Yasuhisa Omura

11:10-11:40

- SP01 **<Invited> Compatibility of Ferroelectric Memory or Functional Memory and System Application for Biomass plantation**  
Hiroshi Nozawa and Yoshiaki Yamanishi,  
(Kyoto University)

11:40-12:10

- SP02 **<Invited> Is the Japan semiconductor industry declining?**  
Daisuke Ueda,  
(Nagoya University)

12:10-12:40

- SP03 **<Invited> Micropower extraction circuits for vibrational energy harvesters --- Tutorial ---**  
Kenji Taniguchi,  
(Osaka University)

**12:40-13:40      Lunch**

**Poster Viewing Session**

Kyoto Hall Lobby

13:40-15:00

**15:00-15:20   Short Break**

**INDUSTRIAL SESSION**

Chair: Masayuki Furuhashi

15:20-16:00

IN11   **<Invited> Polarized light observation of semiconductor wafers for power devices**

Kenta Murayama, Seiya Mizutani, Yuya Mizutani and Shuta Harada,  
(Mipox)

16:00-16:40

IN12   **<Invited> Connect Everything Concept**

Ichiro Kashiwagi,  
(Nissinbo Micro Devices Inc.)

16:40-17:20

IN13   **<Invited> Remote control of doping profile, silicon interface, and gate dielectric reliability via oxygen insertion into silicon channel**

Hideki Takeuchi, Robert J. Mears, Marek Hytha, Daniel Connelly, Paul E. Nicollian  
and Hiu-Yung Wong,  
(Atomera)

**17:20-17:30   Short Break**

**Awards & Closing Remarks**

17:30-17:55   Award Presentation Naohiro Ueda (Nissinbo Micro Devices Inc.)

17:55-18:00   Closing Remarks

Hirobumi Watanabe (W.T.C.)